EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3879	(semiconductor near5 (layer film)) near8 crystalliz$3	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 19:06
L2	641	(semiconductor near5 (layer film)) near10 recrystalliz$3	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 19:06
L3	6163	(silicon near5 (layer film)) near8 crystalliz$3	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 19:07
L4	1245	(silicon near5 (layer film)) near10 recrystalliz$3	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 19:07
L5	378	3 and 4	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 15:39
L6	280	1 and 2	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 15:40
L7	587	5 6	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 15:40
L8	438	7 and (gate near8 (insulat$3 dielectric))	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 19:08
L9	176	8 and ((dop$3 implant$3 impurity) near15 (recrystalliz$3 crystalliz$3))	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 18:17
L11	2438	(semiconductor same (layer film)) same crystalliz$3	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 19:06
L12	555	(semiconductor same (layer film)) same recrystalliz$3	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 19:06

L13	2550	(silicon same (layer film)) same crystalliz$3	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/05/24 19:07
L14	677	(silicon same (layer film)) same recrystalliz$3	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/05/24 19:07
L15	49	11 and 12	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/05/24 19:07
L16	49	13 and 14	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/05/24 19:08
L17	88	15 16	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/05/24 19:08
L18	18	17 and (gate same (insulat$3 dielectric))	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/05/24 19:08